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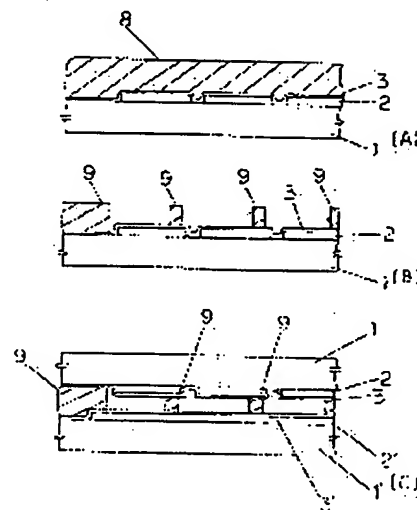
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(54) METHOD FOR FORMING LIQUID CRYSTAL ELECTROOPTICAL DEVICE

(57)Abstract:

PURPOSE: To control a space between two orientation films to a prescribed thickness with scattering of $\pm 0.5\mu\text{m}$ by controlling a height of the orientated film to the prescribed height by remaining selectively an epoxy adhesives, and by forming a spacer and the peripheral sealing agent with the epoxy adhesives which is the same material to that of the spacer and sealing agent.

CONSTITUTION: The titled device is formed by coating with the org. adhesives 8 such as the epoxy adhesives having photosensitive property on the one surface of the substrate 1 which forms an electrode 2, or forms an orientated film 3, thereon, in the prescribed height by means of a coating method followed by selectively exposing it with a mask to expose the photosensitive resin. The spacer 9 and the peripheral sealing part having a linear type, a block type or an optional adductor type are selectively formed by an etching step, after selectively exposing only a range which is not masked. Thus, even in case that the resin of acting as the spacer and the peripheral sealing agent of a cell has the unevenness in height, the coating film of the prescribed thickness with scattering of less than $\pm 0.5\mu\text{m}$ is obtd. by selectively remaining the coating film which is the same material to that of the spacer and sealing agent.



LEGAL STATUS

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